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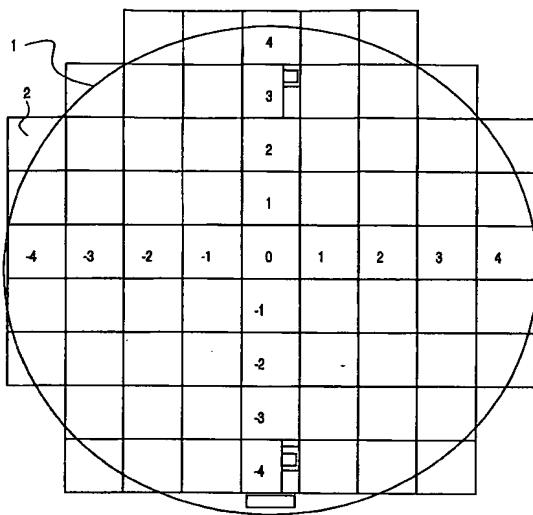
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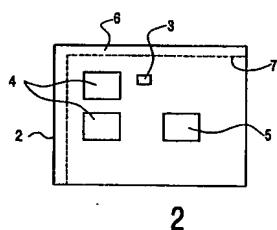
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(54) Title: METHOD OF PRODUCING SEMICONDUCTOR ELEMENTS USING A TEST STRUCTURE



(57) Abstract: Testing the production of semiconductor elements on a substrate, the semiconductor elements having a plurality of cell types, by providing at least one test structure on the substrate with a number of test cells having cell types similar to one or more of the plurality of cell types, each of the cell types having at least a first and a second local interconnect layer structure to be connected to predetermined supply voltages during use, a plurality of first and second polysilicon layer structures to provide control voltages to first and second electronic component structures, respectively, connecting in the test structure all of the plurality of first polysilicon layer structures to one another to provide an interconnected first polysilicon layer structure, and connecting in the test structure all of the plurality of second polysilicon layer structures to one another to provide an interconnected second polysilicon layer structure, providing predetermined test voltages and measuring currents resulting from the test voltages to identify production errors.





SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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